

ABSTRACT OF THE DISCLOSURE

A semiconductor device wherein in formation of the wiring connection, an opening is made up to the middle of the insulating film, a side wall is formed, a burying wiring with the lower portion is arranged, a pad is formed, and a pad is formed in a polyplug contact without a masking step. Further, a conductive material is filled in the hole in the insulating film, a hole is opened in this material, a side wall is formed on the inner wall, a shrunken contact is opened by using this as a mask, and the conductive material is filled.